A dm ixtures to d-wave gap symmetry in untwinned YBa₂Cu₃O₇ superconducting lm s measured by angle-resolved electron tunneling

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We report on an ab-anisotropy of $J_{ckb}=J_{cka}=1.8$ and $I_cR_{n\,kb}=I_cR_{n\,ka}=1.2$ in ram p-edge junctions between untwinned YBa_2Cu_3O_7 and s-wave Nb. For these junctions, the angle with the YBa_2Cu_3O_7 crystalb-axis is varied as a single parameter. The R_nA ()-dependence presents 2-fold sym metry. The minim a in I_cR_n at $=50\,$ suggest a real s-wave subdom inant component and negligible d_{xy} -wave or in aginary s-wave admixtures. The I_cR_n ()-dependence is well-tted by 83% d_{x^2-y} -7, 15% isotropic s- and 2% anisotropic s-wave order parameter symmetry, consistent with $_b=$ a = 1.5.

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Phase-sensitive experiments^{1,2} and tunnel spectroscopy³ have provided rich evidence for the sign change of the pair wave function in the crystal abplane of high-T_c superconductors. Insight in the extent of subdom inant adm ixtures to the $d_{x^2 \ y^2}$ -wave symmetry is less well established. They are of high importance for the basic understanding of high-T_c superconductivity and the design of novel d-wave based Josephson devices, but also for standard high-T_c junctions. They determ ine for instance the exact position of the nodes, and the am ount of ab-anisotropy.

In $YBa_2Cu_3O_7$ strong anisotropy in the electronic structure has been reported, which can be interpreted as an e ective mass anisotropy along the a- and baxes: An elongated vortex shape by scanning tunneling spectroscopy⁴ suggests 50% anisotropy. Sixty percent anisotropy is found in the London penetration depth by far-infrared spectroscopy,⁵ as well as using caxis YBa₂Cu₃O₇/Pb Josephson junctions with a magnetic eld oriented parallel to the a-or b-axis⁶. O ther studies, neutron scattering on ux-line lattices and single crystal torque-m easurem ents,⁸ indicate a sm aller anisotropy of 12. Related, surface impedance⁹ and resistivity measurements¹⁰ demonstrate an anisotropy of 1:5 to 1:6 and a= b 1:5 respectively. R_{ska}=R_{skb}

A lso, in plications for the anisotropy of the superconducting gap have been discussed. R am an scattering¹¹ evidences a real isotropic s-wave admixture of 5%; them all conductivity measurements in a rotating magnetic eld² place a maximum of 10% based on the node positions. A ngle-resolved photoemission spectroscopy (ARPES)¹³ indicates larger ab-anisotropy of $_{\rm b}$ = $_{\rm a}$ = 1.5. The use of untwinned single-crystals is considered crucial in all these studies. However, clear consensus on subdom – inant order parameter symmetries is not reached, nor is detailed angle-resolved data in the ab-plane of thin

In s available, although rst attempts on twinned In s have been performed.¹⁴ In view of this, we present here new results on the anisotropy, comparing untwinned and twinned YB a_2 C u_3 O₇.



FIG.1: (Color online) Angle-resolved electron tunneling with YBa₂Cu₃O₇/Au/Nb ram p-type junctions oriented every 5 over 360. The YBa₂Cu₃O₇ base-electrode (red) is covered by SrT iO₃ insulator (green), and contacted by a Au barrier (not visible) and a Nb counter-electrode (blue). The arrows (white) indicate the main crystal orientations in the ab-plane of the high- T_c superconducting material.

In untwinned $YBa_2Cu_3O_7$ thin lm s, the usual Yandom ' exchange of the a- and b-axis is eliminated. This enables to study the electronic properties angle-resolved in the ab-plane. The experimental layout is summarized in Fig. 1. Basically, the $YBa_2Cu_3O_7$ base-electrode is patterned into a nearly circular polygon, changing the orientation from side to side by 5 degrees. A Au barrier and Nb counter-electrode contact each side. In this way, the angle with respect to the (010)-orientation is varied as a single parameter.

First, bilayers of 170 nm YBa₂Cu₃O₇ and 100 nm SrT iO₃ are grown by pulsed-laser deposition (PLD) on single-crystal SrT iO₃ substrates. The YBa₂Cu₃O₇ Im s are optim ally doped, with $T_{c;0}$ 89 K.Ramps are ion-milled in the bilayers using a photo resist stencil. To assure equivalent ramp quality over 360, the sample stage is rotated around the substrate norm al, while maintaining the angle of incidence of the Ar-ion beam constant at 40 with the substrate plane. The resulting ramp-angle

	tw inned	untw inned
SrTiO ₃ : /	0.12 /119.0	1.07 / 357.9
$YBa_2Cu_3O_7$: /	0.20 / 97.3	0.75 / 346.3
a	3.866(3)	3.849 (6)
CellPar.(A) b	3.867 (4)	3.892 (7)
С	11.678(3)	11.703(7)

TABLE I: Vicinalangle and its orientation of the SrT iO $_3$ substrates and YBa₂Cu₃O₇ lm s. The YBa₂Cu₃O₇ data is obtained after device completion.

with the substrate plane is $_{\rm R} = 30$. On a m icroscopic scale the interfaces m ay present som e faceting, albeit less than in e.g. grain boundaries. This faceting is not expected to a ect the main conclusions of the presented studies. A fler rem oval of the photo-resist stencil and a short 90 -incidence ion-m ill for cleaning purposes, a 5 nm YBa₂Cu₃O₇ interlayer¹⁵ is deposited to prepare an insitu interface to a 30 nm Au barrier form ed also by PLD. Then, a 160 nm thick Nb counter-electrode is dc-sputter deposited through a lift-o stencil. Special care is taken to obtain a clean Au/Nb interface by a 50 s rf-plasm a etch just before Nb deposition. A fler lift-o , redundant Au and YBa₂Cu₃O₇ interlayer m aterial is rem oved by A r-ion m illing. The junctions are 4 m wide.

The twin behavior of (001)-YBa₂Cu₃O₇ In s is in uenced by the substrate vicinal angle and its in-plane orientation ¹⁶ Here, is de ned between the crystallographic and optical substrate-norm al, and describes the in-plane orientation with respect to the SrT iO $_3$ h100i crystal axis. The degree of twinning can be controlled from completely untwinned to the presence of four aborientations, varying from 1:1 to a small vicinal angle (0:1), where = 0. For = 1:1, grow th with the b-axis along the step-ledges is induced, and only one crystal orientation is present. On the contrary, 4 tw in orientations are present for sm all vicinal angle substrates. The twin orientations have pair-wise their inplane diagonal of the YBa2Cu3O7 crystal aligned with each substrate diagonal, so that a- and b-axes and vice versa are arranged nearly in parallel.¹⁶ A fter com pletion of the device, the $YBa_2Cu_3O_7$ base-electrode is exam ined with X-ray di raction (XRD). An average of the a and bunit cell dimensions is found for twinned Ims (see Table I). For untwinned Ims, the individual a and b unit cell parameters can be distinguished and are close to single-crystal values. Detailed hk-scans of the (034) re ections show 4 di erent orientations for YB_gCu₃O₇

In s grown on small vicinal angle substrates (Fig.2a), associated with the above-mentioned 4 tw in orientations. For Ins grown on substrates with = 1:1 however, only one orientation is present (Fig.2b).

The XRD and electrical data presented in this article correspond to the sam e sam ples. Figure 3 presents the electrical characterization of the twinned base-electrode sam ple (a-c), and the untwinned one (d-f,h). During the m easurem ent, the m agnetically shielded sam ple space re2



FIG.2: (Color online) Logarithm ic contour plots of hk-scans nearthe $(0\overline{3}4)$ re ection of YBa₂Cu₃O₇: (a) grown on a sm all vicinal angle SrT iO₃ substrate (0.12), and (b) grown on an = 1.07 and = 2.1 vicinal SrT iO₃ substrate. Both scans are measured after device completion.

duces background elds below 0.1 T. Trapped ux in or near the junctions is excluded by systematic I_c (B) m easurem ents, assuring a correctly determ ined critical current density (J_c) . The superconducting properties of the Au/Nb bilayer are independent of the orientation. Therefore, J_c depends on the in-plane orientation with respect to the b-axis of the $YBa_2Cu_3O_7$ crystal only, and presents four maxim a for both samples, approaching zero in between. This is in agreem ent with predom inant $d_{x^2 - v^2}$ -w ave symmetry of the superconducting wave function in one electrode only, and a cos(2)-dependence is expected $\mathbf{.}^{17}$ In closer detail, the nodes of the untw inned $YBa_2Cu_3O_7$ sam pleare found at 5 from the diagonal between the a-and b-axis. This presents direct evidence for a signi cant realisotropic s-wave admixture. A rst estim ate for the s-over $d_{x^2 y^2}$ -w ave gap-ratio is calculated as $j\cos(2_0)j = 17\%$ for a node angle $_0 = 50$. For the tw inned base-electrode, the nodes are found at the diagonal, which is expected if all twin orientations are equally present, and contributions of subdom inant components average out to zero.

The suppressed J_c in the nodal direction (0.01 J_{kh010i}) suggests small, if not absent, im aginary admixtures,¹⁸ for instance of isotropic is-wave or id_{xy}-wave type which in contrast would lift the nodes. A signi cant real d_y -wave admixture is excluded, because this would induce a rotation in the same direction with respect to the crystal of all nodes.

In the untwinned case, the J_c -value is 1.8 times larger in the b-than in the a-direction. Preparation elects can be eliminated, since circular symmetry with respect to the substrate norm all has been conserved at all phases of the fabrication. The norm all-state resistance (R_nA) is lower along the b-than along the a-axis, and presents a two-fold symmetry axis for the untwinned case. Using the angle-resolved values, the anisotropy in the I_cR_n -product amounts to $I_cR_{nkb}=I_cR_{nka}=1.22$.

To estimate the I_cR_n -products in our junctions, we model them as SINS' structures, where S is YBa₂Cu₃O₇, I is the YBa₂Cu₃O₇/Au interface barrier, which has much higher resistance than the Au (N) and the Au/Nb



FIG. 3: (Color online) J_c , R_nA , and I_cR_n -product vs the junction orientation with respect to the YBa₂Cu₃O₇ crystal for tw inned (a-c), and untw inned (d-f_n) YBa₂Cu₃O₇ at T = 4.2 K and in zero magnetic eld. (see text for description ts) (g) F it parameter evolution for untw inned case, and (h) corresponding ts.

(N/S') interface. From independent resistance measurements on our PLD Au ($_{Au} = 4.6$ cm at 4.2 K), the mean-free-path is $l_{Au} = 18 \text{ nm}$, and the dirty-lim it coherence length is $A_u = 49 \text{ nm}$. Using these values and the YBa2Cu3O7/Au interface resis-10⁸ cm^2 , the transparency at tance R_BA_{Y=Au} this interface is low: 440, where $_{\rm B}$ = B_{Y=Au} $R_B A = A_u A_u$.¹⁹ From a small Ferm i-velocity m ism atch, we estimate the Au/Nb interface transparency much larger, $B_{A_u=N_b}$ < 20. The electrode-separation is d_{A_u} = 26 nm for 30 nm thick Au and ram p angle $_{\rm R}$ = 30. Since $l_{Au} < d_{Au}$ and $l_{Au} < Au$, Au is in the diusive regime, while YBa₂Cu₃O₇ is in the clean lim it with the anisotropic gap function Y.

W e extend the expression for the supercurrent in di usive SINS' structures¹⁹ to our case of a low -transparent junction between a clean d-wave superconductor and a di usive NS' bilayer. The contribution of midgap Andreev bound states is small in such a junction²⁰ and can be neglected.

$$I_{s}R_{n} = \frac{1}{N} \int_{N}^{22} d d \sin() D \sin(')$$
 (1)

$$= \frac{2 k_{\rm B} T}{e} \frac{\chi^{\rm A}}{n=0} \frac{p - \chi^{\rm Y}}{\frac{2}{2} + \frac{1}{2}n^{\rm P}} \frac{\chi^{\rm Y}}{\frac{2}{2} + \frac{1}{2}n^{\rm P}}$$
(2)

$$= \frac{K_{\rm B} T_{\rm CN \ b \ N \ b}}{K_{\rm B} T_{\rm CN \ b} + B_{\rm A \ u = N \ b} (d_{\rm A \ u} = A_{\rm u})} \frac{p_{\rm c}}{2 + \frac{1}{2} + \frac{1}{2}}$$
(3)

 $\operatorname{Here}_{\mathsf{RR}}$ is the angle with the interface normal, and d d sin ()D is the norm alization constant. The N = integration is performed over angles = 0 to 2, and = 0 to $\frac{1}{2}$ of a half-sphere of all trajectories: for each junction orientation, and taking the crystal orientation and ram p-angle into account. The barrier transm ission $\cos \operatorname{cient} D = \cos() \exp[f1]$ \cos^1 ()q] is in the $\lim it of a \ sm \ all \ YBa_2Cu_3O_7$ Ferm ivelocity, where describes the tunnel-cone size. The sum in Eq.(2,3) is taken over the M atsubara frequencies $!_n = T(2n + 1)$. is the anisotropic gap function in $YBa_2Cu_3O_7$, and is the isotropic proxim ity-induced gap function in Au. $_{\rm N \ b}$ and T_{cN b} are the bulk pair potential and the critical tem perature of Nb, respectively. The critical current Ic and $I_{\rm c}R_{\rm n}$ -product should be found by calculating a m axim um of IsR_n over the phase di erence ' across the junction.

Tunneling along the a- and b-axis may then be compared theoretically in terms of the ratio = $I_c R_{nkb} = I_c R_{nka}$. Using Eqs.(1-3), it can be shown that for constant properties of the N b/A u bilayer, the ratio of the Y B $a_2 C u_3 O_7$ gap for these directions is $_{Y kb} = _{Y ka}$ Therefore, the observed anisotropy of = 1.22 represents a lower lim it for this gap ratio, which is valid for extrem ely small ratios $_{Y} = _{N b}$ 0.1. For increasing ratio $_{Y} = _{N b}$; the value = 1.22 requires a rapid increase of $_{Y kb} / _{Y ka}$. In this estimate, depends only on the gap ratios and on the Au/Nb interface transparency.

The anisotropic gap in Y B a_2 C u_3 O $_7$ depends on the inplane angle (0 to 2), and the angle ($\frac{1}{2}$ to $\frac{1}{2}$) with the ab-plane. Various possible symmetry functions exist to describe this gap. Here, we consider the following 3D gap function in Y B a_2 C u_3 O $_7$ consisting of a dom inant $d_{x^2\ y^2}$ – wave component with an isotropic and an anisotropic s-wave admixture:

$$X^{2} = Y_{0} \cos^{2}() c_{i} f \cos^{2}() \sin^{2}() g^{i}$$
 (4)

with the coe cients $c_1 > c_0$; c_2 and $c_1 + c_0 + c_2 = 1$. Here $_{Y_0}$ denotes the magnitude of the YBa₂Cu₃O₇ gap at the interface. Consistent with our earlier estimate $_{Ykb}=_{Yka} > 1.22$, the gap-ratio is taken as $_{Ykb}=_{Yka} = 1.5$ in agreement both with the observed node positions and ARPES.¹³ W ith this, the coe cients are found from the t to the data g = 0.15, $c_1 = 0.83$ and $c_2 = 0.02$. O ther choices for the gap symmetry functions lead to slightly di erent num bers but will not alter the basic results of our calculations.

A series of ts is presented in Fig.3h: the wider the tunneling cone (sm aller), the sm aller is the width of the oscillations in the $I_{\rm c}R_{\rm n}$ ()-dependence (arrow). The e ective $Y B_{2}Cu_{3}O_{7}$ gap Y_{0} and $B_{A_{u=N,b}}$ must then becom e larger. This dependence is presented in Fig. 3g. Them in in um value Yo occurs for norm al-incidence tunneling (lim ! 1), so that $_{Y_0}$ 6.4 m eV . For reasonable Y_0 values (< 0.5 eV), $B_{Au=Nb}$ varies from 13.6 to about 18. This gives an estim ate for the Au/Nb interface resistance: $R_B A = 0.36$ 0.05 n cm². In contrast to $B_{A,u=N,b}$, it is not possible to give an accurate estim at for the YB a_2 C u_3 O $_7$ gap from our data. Therefore, we choose to t the data with $Y_0 = 44 \text{ meV}$, $B_{Au=Nb} = 16:8 \text{ in}$ Figs. 3c and 3f. These are not claim ed to be the correct values; the simulation demonstrates how ever that large Y_0 may well be consistent with small $I_c R_n$ values. For the untwinned case = 18:4, corresponding to a tunnel cone with a full-width-half-maximum (FW HM) of 31:0 (cosine-term of D not included). For the twinned case, the $I_c R_n$ ()-dependence is simulated with the same param eters, except for a slightly sm aller cone (= 263, FW HM = 26:0), and assuming equal presence of both twin orientations: $\frac{1}{2}$ [I_cR_n () + I_cR_n (+ $\frac{1}{2}$)]. The smaller tunnel cone for the twinned case is consistent with higher $R_{\,n}A\,\text{-}$ and lower $J_{\rm c}\,\text{-values.}\,$ This may result from a slightly thicker tunnel barrier at the YBa2Cu3O7/Au interface, e.g., due to minor variations in the Au PLDconditions, modifying this interface.

The R_nA ()-dependence is tted with an ellipsoidal relation of the conductivity projections along the main

crystal directions of the YBa2Cu3O7. W ritten in terms of the R_nA values along these directions, this gives $R_n A_{kb}^2 \cos^2() + R_n A_{ka}^2 \sin^2()$. Fig. 3e $R_nA() =$ shows the result using $R_n A_{ka} = 44$ n cm² and $R_n A_{kb} = 29 \text{ n} \text{ cm}^2$. For the twinned case, a geom etrical average of the conductivities is assumed, $R_nA() = 2 = [R_nA^{-1}() + R_nA^{-1}(+ \frac{1}{2})]$. The used values in Fig. 3b read $R_n A_{ka} = 141 \text{ n} \text{ cm}^2$, $R_n A_{kb} =$ $47 \text{ n} \text{ cm}^2$. A lthough these phenom enological ts are indicative, angle-resolved calculations including aspects of the YBa₂Cu₃O₇ band-structure and band-bending e ects are needed for a detailed understanding. Finally, the $J_{c}()$ ts are obtained with the ratios of the $\mathbb{R}_{n}()$ - and the $R_n A$ ()-dependencies, the ensemble of which gives a consistent simulation of the angle-resolved junction properties.

The experimental results support theories based on a 2-band model of the chains and planes^{21,22} modeled with a symmetric, anti-symmetric and isotropic component. Furtherm ore, our ndings agree with c-axis tunneling from two twinned YBa2Cu3O7 grains to a Pb counter-electrode that depends on the magnetic eld orientation,23 and angle-dependence studies on grain boundary junctions.²⁴ For allhigh-T_c junctions and circuits, we mark the anisotropy as a possible intrinsic source of their lim ited reproducibility: both twin orientations m ay not be uniform ly present, yielding an im portant variation in J_c. Controlover the crystal orientation then presents a key to im provem ent. A nother im portant aspect concerns the nodes at 5 from the hllli crystal direction. The best choice for the electrode-orientation of devices aim ing a d-wave induced second harm onic in the current-phase relation, such as $\frac{1}{2}$ -SQUD s based on grain boundary junctions, may therefore deviate from the h110i crystal direction.

In conclusion, an angle-resolved electron tunneling study using Josephson junctions with an untwinned YBa₂Cu₃O₇ base-electrode is presented. Evidence for signi cant in-plane anisotropy in the electronic properties of YBa₂Cu₃O₇ is found.

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- ⁸ T.Ishida et al., Physica C 263, 260 (1996).
- ⁹ K.Zhang et al, Phys.Rev.Lett. 73, 2484 (1994).
- ¹⁰ T.A.Friedmann et al., Phys. Rev. B 42, 6217 (1990).
- ¹¹ M.F.Lim onov et al, Phys.Rev.Lett. 80, 825 (1998).
- ¹² H.Aubin et al, Phys. Rev. Lett. 78, 2624 (1997).
- ¹³ D.H.Lu et al, Phys. Rev. Lett. 86, 4370 (2001).
- ¹⁴ D.J.van Harlingen et al., Physica C 317-318, 410 (1999).

¹ D.A.W ollm ann et al., Phys.Rev.Lett. 71, 2134 (1993).

² C.C.T sueiet al, Phys. Rev. Lett. 73, 593 (1994).

³ J.Y.T.W eiet al, Phys.Rev.Lett. 81, 2542 (1998).

⁴ I. Maggio-Aprile et al., Phys. Rev. Lett. 75, 2754 (1995).

⁵ D.N.Basov et al, Phys.Rev.Lett. 74, 598 (1995)

⁶ A.G.Sun et al, Phys.Rev.B 52, R15731 (1995).

⁷ S.T. Johnson et al, Phys. Rev. Lett. 82, 2792 (1999).

- ¹⁵ H.J.H.Sm ible et al, Appl. Phys. Lett. 80, 4579 (2002).
 ¹⁶ J.M.D ekkers et al, Appl. Phys. Lett. 83, 5199 (2003).
- ¹⁷ M.Sigrist, T.M. Rice, J.Phys.Soc.Jpn.61, 4283 (1992).
- ¹⁸ D.J. van Harlingen, Rev. M od. Phys. 67, 515 (1995).
- ¹⁹ A.A.Golubov et al, Phys. Rev. B 51, 1073 (1995).
- ²⁰ R.A.Riedel, P.F.Bagwell, Phys. Rev. B 57, 6084 (1998).
- ²¹ I.I.Mazin, A.A.Golubov, A.D.Zaikin, Phys.Rev.Lett. 75,2574 (1995).
- ²² C.O'Donovan et al, Phys. Rev. B 55, 9088 (1997).
- ²³ K.A.Kouznetsov et al, Phys.Rev.Lett. 79, 3050 (1997).
- ²⁴ F.Lom bardiet al, Phys. Rev. Lett 89, 207001 (2002).